

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ECH8654 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Halogen free compliance

- 1.8V drive
- · Protection diode in

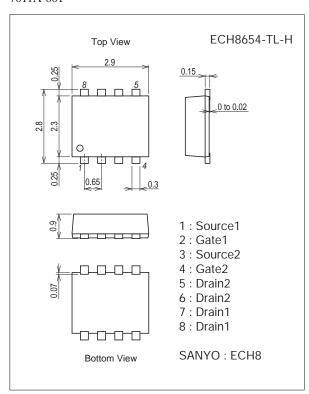
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	ID		-5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-40	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm) 1unit	1.3	W
Total Power Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-001



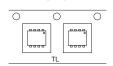
Product & Package Information

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

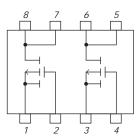
Packing Type: TL



Marking



Electrical Connection

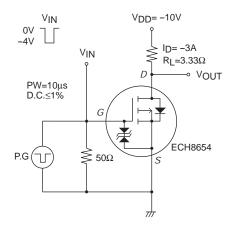


ECH8654

Electrical Characteristics at Ta=25°C

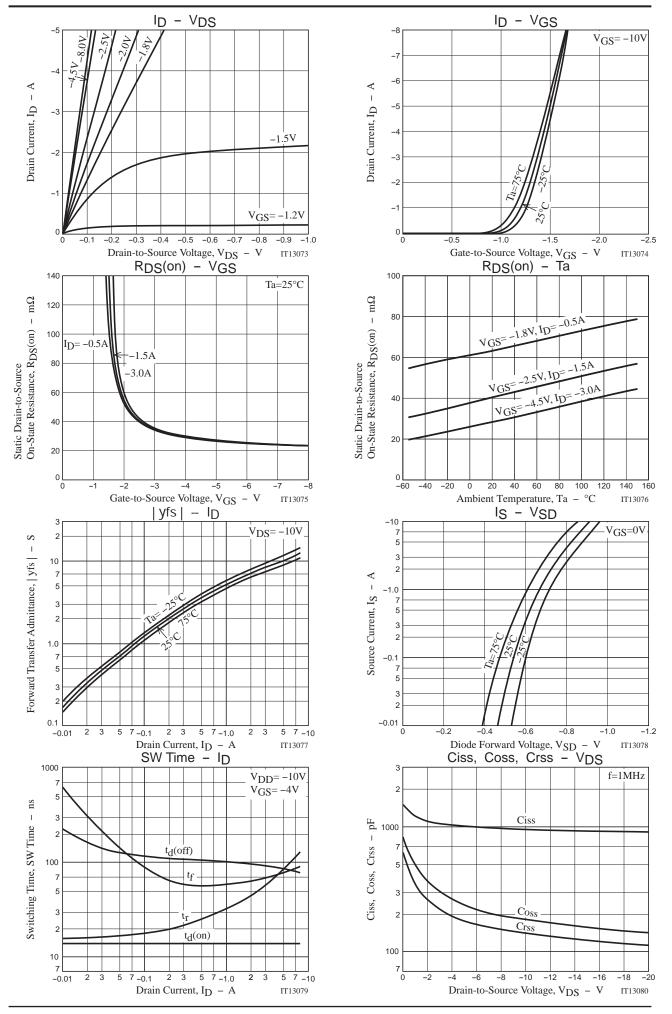
Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Uniii	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-3A	4.9	8.3		S	
	R _{DS} (on)1	I _D =-3A, V _G S=-4.5V		29	38	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =-1.5A, V _G S=-2.5V		41	58	$m\Omega$	
	R _{DS} (on)3	I _D =-0.5A, V _G S=-1.8V		64	98	mΩ	
Input Capacitance	Ciss			960		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		180		pF	
Reverse Transfer Capacitance	Crss			140		pF	
Turn-ON Delay Time	t _d (on)			14		ns	
Rise Time	t _r	Constitution of the state of th		55		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		92		ns	
Fall Time	tf			68		ns	
Total Gate Charge	Qg			11		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-5A		2.0		nC	
Gate-to-Drain "Miller" Charge	Qgd	_		2.8		nC	
Diode Forward Voltage	V _{SD}	I _S =-5A, V _{GS} =0V		-0.82	-1.2	V	

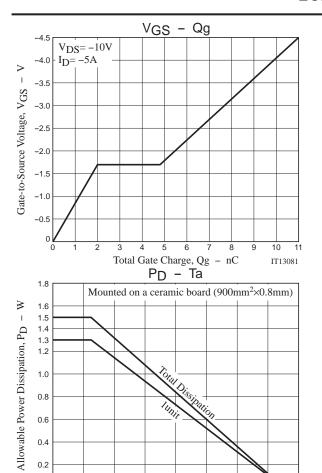
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo	
ECH8654-TL-H	CH8654-TL-H ECH8		Pb Free and Halogen Free	





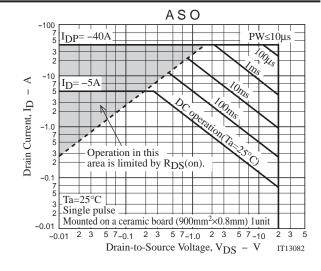
40 60 80 100 120 Ambient Temperature, Ta - °C 160

IT13083

0

0

20

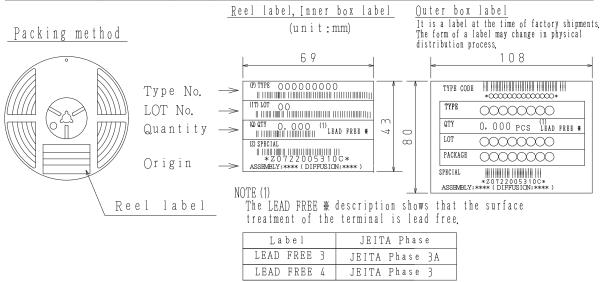


Embossed Taping Specification

ECH8654-TL-H

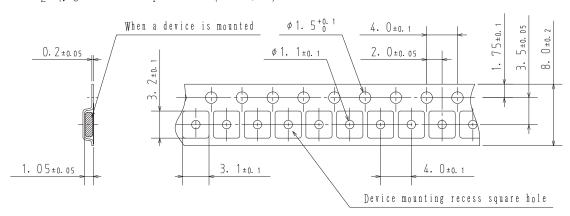
1. Packing Format

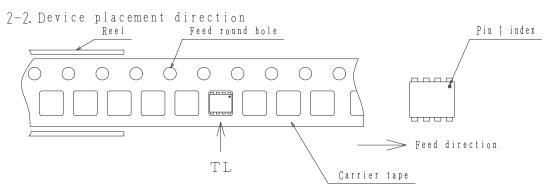
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

2-1. Carrier tape size (unit:mm)

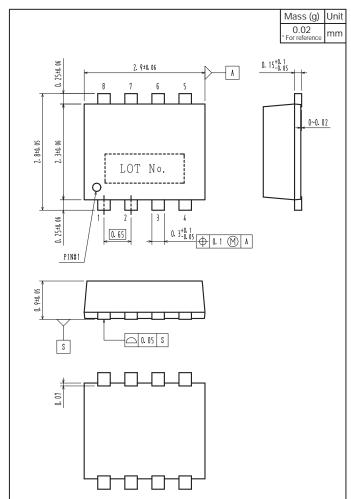




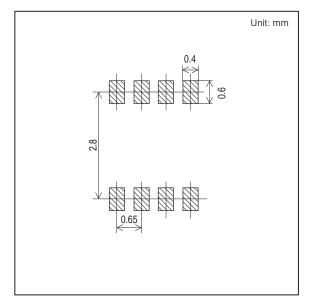
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8654-TL-H



Land Pattern Example



Note on usage: Since the ECH8654 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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